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Substitute for form 1449A/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/075,390		
		Filing Date	February 15, 2002		
		First Named Inventor	Kristy A. Campbell		
		Art Unit	2818		
		Examiner Name	Not Yet Assigned		
Sheet	1	of	1	Attorney Docket Number	M4065.0505/P505

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
NOR	A	5,761,115-	06-02-1998	Kozicki et al.	
NOR	B	5,837,564-	11-17-1998	Sandhu et al.	
NOR	C	5,896,312-	04-20-1999	Kozicki et al.	
NOR	D	5,914,893-	06-22-1999	Kozicki et al.	
NOR	E	6,084,796-	07-04-2000	Kozicki et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that Issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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NOR	F	P. Boolchand, et al. - "Onset of Rigidity in Steps in Chalcogenide Glasses" Properties and Applications of Amorphous Materials, pgs. 118-124.	

Examiner Signature		Date Considered	4/13/04
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		Number*Kind Code* (if known)			
NR	AA	6,388,324	05/14/2002	Kozicki et al.	
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NR	BA	WO 02/21542	03/14/2002	Kozicki et al.		
NR	BB	WO 00/48196	08/17/2000	Kozicki et al.		
NR	BC	WO 97/48032	12/18/1997	Kozicki et al.		
NR	BD	WO 99/28914	06/10/1999	Kozicki et al.		

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MDZ	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.	
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				Examiner Name	Not Yet Assigned
Sheet	3	of	8	Attorney Docket Number	M4065.0505/P505

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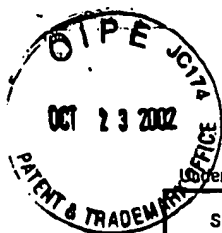
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/075,390
		Filing Date	February 15, 2002
		First Named Inventor	Kristy A. Campbell
		Group Art Unit	2818
		Examiner Name	Not Yet Assigned
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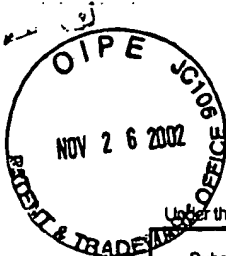
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Examiner Signature	<i>u s d p z</i>	Date Considered	4/13/04
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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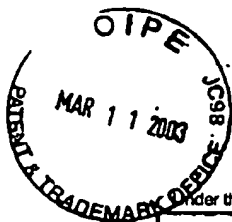
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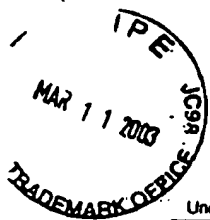
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W	AU1	2003/0001229 APP	1/2/2003	Moore et al.	
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W	BA	56	126916	10/19981	Akira et al.	
	BB					

Examiner Signature	<i>W. S. R. R.</i>	Date Considered	4/13/04
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/075,390
				Filing Date	July 10, 2002
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2818
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	M4065.0695/P695
Sheet	4	of	4		

[illegible]

Examiner Signature	<i>[Signature]</i>	Date Considered	4/13/04
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